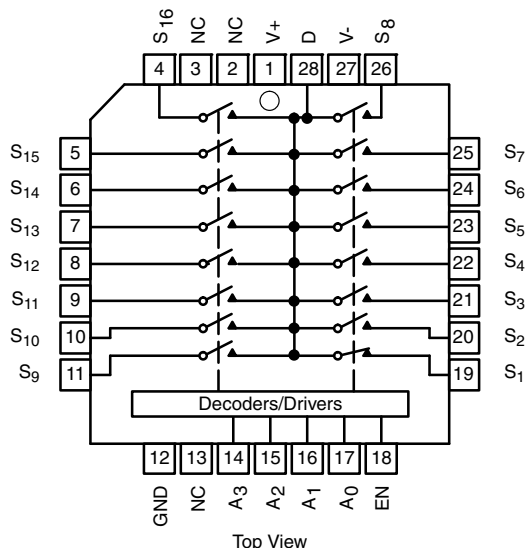
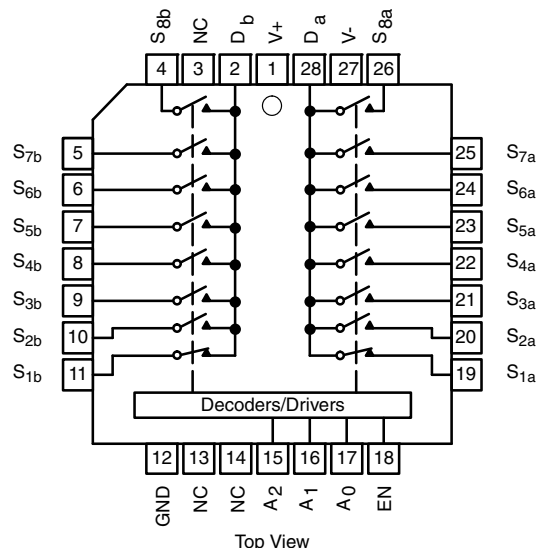


FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION
DG406
PLCC and LCC

DG407
PLCC and LCC

TRUTH TABLE (DG406)

A ₃	A ₂	A ₁	A ₀	EN	ON SWITCH
X	X	X	X	0	None
0	0	0	0	1	1
0	0	0	1	1	2
0	0	1	0	1	3
0	0	1	1	1	4
0	1	0	0	1	5
0	1	0	1	1	6
0	1	1	0	1	7
0	1	1	1	1	8
1	0	0	0	1	9
1	0	0	1	1	10
1	0	1	0	1	11
1	0	1	1	1	12
1	1	0	0	1	13
1	1	0	1	1	14
1	1	1	0	1	15
1	1	1	1	1	16

TRUTH TABLE (DG407)

A ₂	A ₁	A ₀	EN	ON SWITCH PAIR
X	X	X	0	None
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

Notes

- Logic "0" = $V_{AL} \leq 0.8\text{ V}$
- Logic "1" = $V_{AH} \geq 2.4\text{ V}$
- X = Do not Care

ORDERING INFORMATION (DG406)

TEMP. RANGE	PACKAGE	PART NUMBER
-40 °C to 85 °C	28-Pin Plastic DIP	DG406DJ, DG406DJ-E3
	28-Pin PLCC	DG406DN, DG406DN-T1-E3
	28-Pin Widebody SOIC	DG406DW, DG406DW-E3, DG406DW-T1-E3

Note

- T1 indicates Tape and Reel, -E3 indicates Lead-Free and RoHS Compliant, NO -E3 indicates standard Tin/Lead finish.

ORDERING INFORMATION (DG407)

TEMP. RANGE	PACKAGE	PART NUMBER
-40 °C to 85 °C	28-Pin Plastic DIP	DG407DJ, DG407DJ-E3
	28-Pin PLCC	DG407DN, DG407DN-T1-E3
	28-Pin Widebody SOIC	DG407DW, DG407DW-E3, DG407DW-T1-E3



ABSOLUTE MAXIMUM RATINGS			
PARAMETER		LIMIT	UNIT
Voltages Referenced to V-	V+ to V - ^f	44	V
	GND to V-	-25	
Digital Inputs ^a , V _S , V _D		(V-) - 2 to (V+) + 2 V or 20 mA, whichever occurs first	
Current (Any terminal)		30	mA
Peak Current, S or D (Pulsed at 1 ms, 10 % duty cycle max.)		100	
Storage Temperature	(AK, AZ Suffix)	-65 to 150	°C
	(DJ, DN Suffix)	-65 to 125	
Power Dissipation (Package) ^b	28-Pin Plastic DIP ^b	625	mW
	28-Pin Plastic PLCC ^c	450	
	28-Pin Widebody SOIC	450	

Notes

- a. Signals on SX, DX or INX exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads soldered or welded to PC board.
- c. Derate 6 mW/°C above 75 °C.
- d. Derate 12 mW/°C above 75 °C.
- e. Derate 13.5 mW/°C above 75 °C.
- f. Also applies when V- = GND



SPECIFICATIONS ^a									
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 15 V, V ₋ = -15 V V _{AL} = 0.8 V, V _{AH} = 2.4 V ^f		TEMP. ^b	TYP. ^c	D SUFFIX -40 °C TO 85 °C		UNIT	
						MIN. ^d	MAX. ^d		
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}			Full	-	-15	15	V	
Drain-Source On-Resistance	R _{DS(on)}	V _D = ± 10 V, I _S = -10 mA sequence each switch on		Room	50	-	100	Ω	
				Full	50	-	125		
R _{DS(on)} Matching Between Channels ^g	ΔR _{DS(on)}	V _D = ± 10 V		Room	5	-	-	%	
Source Off Leakage Current	I _{S(off)}	V _{EN} = 0 V V _D = ± 10 V V _S = ± 10 V		Room	0.01	-0.5	0.5	nA	
Drain Off Leakage Current	I _{D(off)}			Full	0.01	-5	5		
				DG406	Room	0.04	-1		1
					Full	0.04	-40		40
				DG407	Room	0.04	-1		1
					Full	0.04	-20		20
Drain On Leakage Current	I _{D(on)}	V _S = V _D = ± 10 sequence each switch on		DG406	Room	0.04	-1	1	
					Full	0.04	-40	40	
				DG407	Room	0.04	-1	1	
					Full	0.04	-20	20	
Digital Control									
Logic High Input Voltage	V _{INH}			Full	-	2.4	-	V	
Logic Low Input Voltage	V _{INL}			Full	-	-	0.8		
Logic High Input Current	I _{AH}	V _A = 2.4 V, 15 V		Full	-	-1	1	μA	
Logic Low Input Current	I _{AL}	V _{EN} = 0 V, 2.4 V, V _A = 0 V		Full	-	-1	1		
Logic Input Capacitance	C _{in}	f = 1 MHz		Room	7	-	-	pF	
Dynamic Characteristics									
Transition Time	t _{TRANS}	see figure 2		Room	200	-	350	ns	
				Full	-	-	450		
Break-Before-Make Interval	t _{OPEN}	see figure 4		Room	50	25	-		
				Full	-	10	-		
Enable Turn-On Time	t _{ON(EN)}	see figure 3		Room	150	-	200		
				Full	-	-	400		
Enable Turn-Off Time	t _{OFF(EN)}			Room	70	-	150		
				Full	-	-	300		
Charge Injection	Q	V _S = 0 V, C _L = 1 nF, R _S = 0 Ω		Room	15	-	-	pC	
Off Isolation ^h	OIRR	V _{EN} = 0 V, R _L = 1 kΩ f = 100 kHz		Room	-69	-	-	dB	
Source Off Capacitance	C _{S(off)}	V _{EN} = 0 V, V _S = 0 V, f = 1 MHz		Room	8	-	-	pF	
Drain Off Capacitance	C _{D(off)}	V _{EN} = 0 V V _D = 0 V f = 1 MHz		Room	130	-	-		
				DG407	Room	65	-		-
DG406	Room			140	-	-			
Drain On Capacitance	C _{D(on)}			DG407	Room	70	-		-
				Power Supplies					
Positive Supply Current	I ₊	V _{EN} = V _A = 0 or 5 V		Room	13	-	30	μA	
Negative Supply Current	I ₋			Full	-	-	75		
				Room	-0.01	-1	-		
				Full	-	-10	-		
		Positive Supply Current	I ₊	V _{EN} = 2.4 V, V _A = 0 V	Room	50	-		500
Full	-				-	700			
Negative Supply Current	I ₋				Room	-0.01	-20		-
					Full	-0.01	-20		-



SPECIFICATIONS _a (for Single Supply)								
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED V ₊ = 12 V, V ₋ = 0 V V _{AL} = 0.8 V, V _{AH} = 2.4 V ^f		TEMP. ^b	TYP. ^c	D SUFFIX -40 °C TO 85 °C		UNIT
						MIN. ^d	MAX. ^d	
Analog Switch								
Analog Signal Range ^e	V _{ANALOG}	V _D = 3 V, 10 V, I _S = -1 mA sequence each switch on		Full	-	0	12	V
Drain-Source On-Resistance	R _{DS(on)}			Room	90	-	120	Ω
R _{DS(on)} Matching Between Channels ^g	ΔR _{DS(on)}			Room	5	-	-	%
Source Off Leakage Current	I _{S(off)}	V _{EN} = 0 V V _D = 10 V or 0.5 V V _S = 0.5 V or 10 V	DG406	Room	0.01	-	-	nA
Drain Off Leakage Current	I _{D(off)}		DG407	Room	0.04	-	-	
Drain On Leakage Current	I _{D(on)}		DG406	Room	0.04	-	-	
			DG407	Room	0.04	-	-	
Dynamic Characteristics								
Switching Time of Multiplexer	t _{OPEN}	V _{S1} = 8 V, V _{S8} = 0 V, V _{IN} = 2.4 V		Room	300	-	450	ns
Enable Turn-On Time	t _{ON(EN)}	V _{INH} = 2.4 V, V _{INL} = 0 V V _{S1} = 5 V		Room	250	-	600	
Enable Turn-Off Time	t _{OFF(EN)}			Room	150	-	300	
Charge Injection	Q	C _L = 1 nF, V _S = 6 V, R _S = 0		Room	20	-	-	pC
Power Supplies								
Positive Supply Current	I ₊	V _{EN} = 0 V or 5 V, V _A = 0 V or 5 V		Room	13	-	30	μA
Negative Supply Current	I ₋			Full	-	-	75	
				Room	-0.01	-20	-	
				Full	-0.01	-20	-	

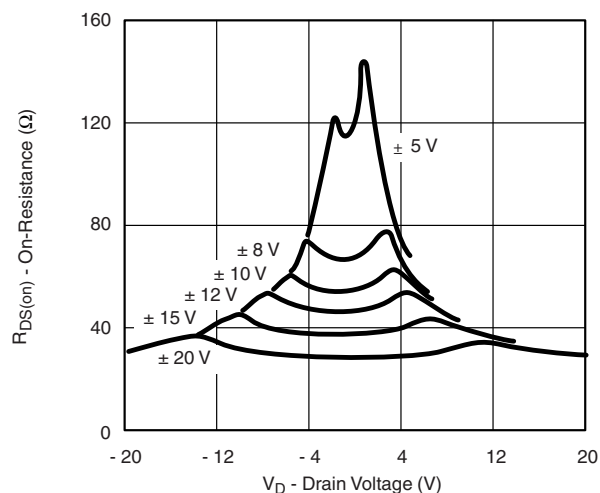
Notes

- Refer to PROCESS OPTION FLOWCHART.
- Room = 25 °C, Full = as determined by the operating temperature suffix.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Guaranteed by design, not subject to production test.
- V_{IN} = input voltage to perform proper function.
- $\Delta R_{DS(on)} = R_{DS(on)} \text{ max.} - R_{DS(on)} \text{ min.}$
- Worst case isolation occurs on Channel 4 due to proximity to the drain pin.

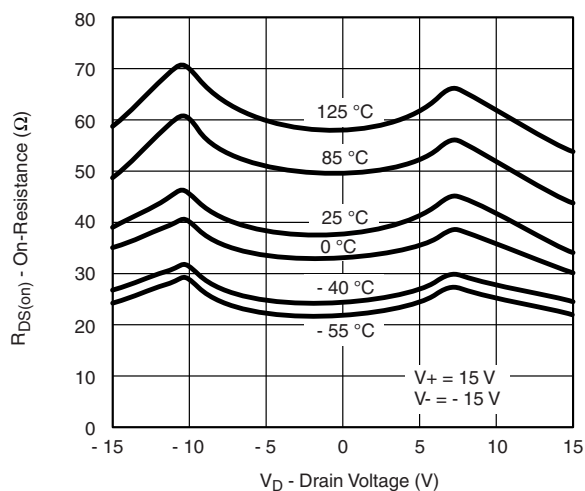
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



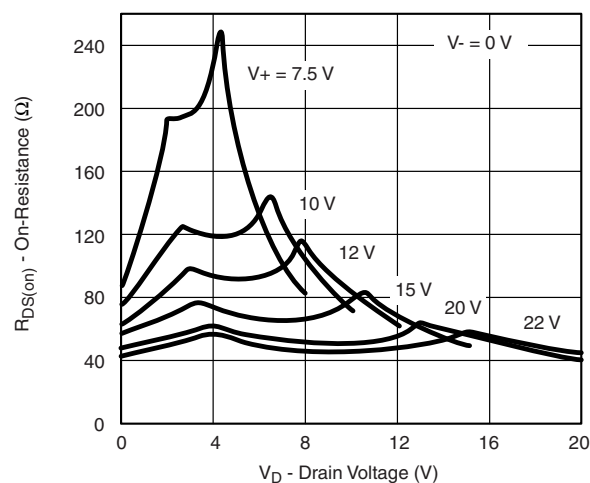
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



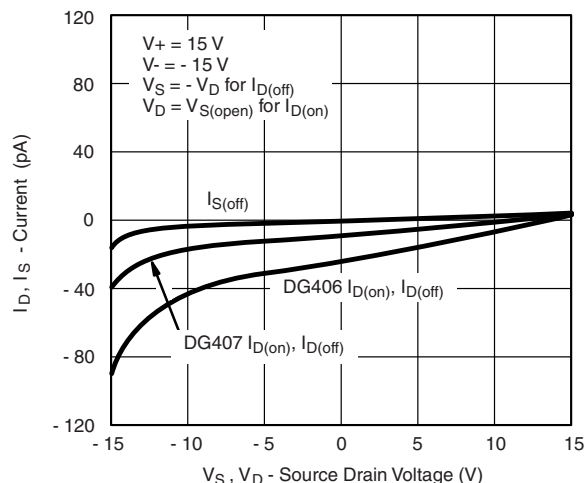
$R_{DS(on)}$ vs. V_D and Supply



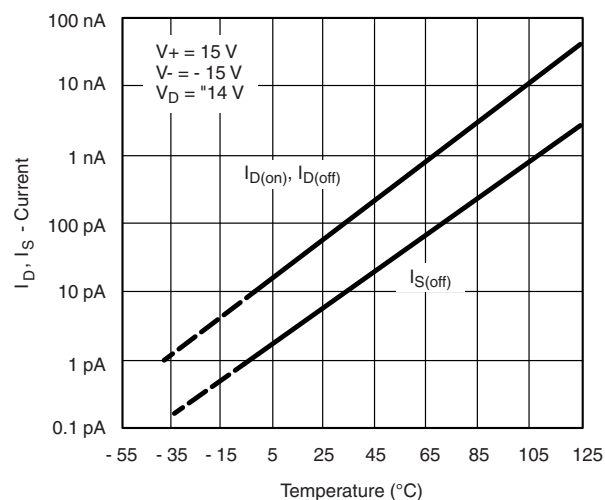
$R_{DS(on)}$ vs. V_D and Temperature



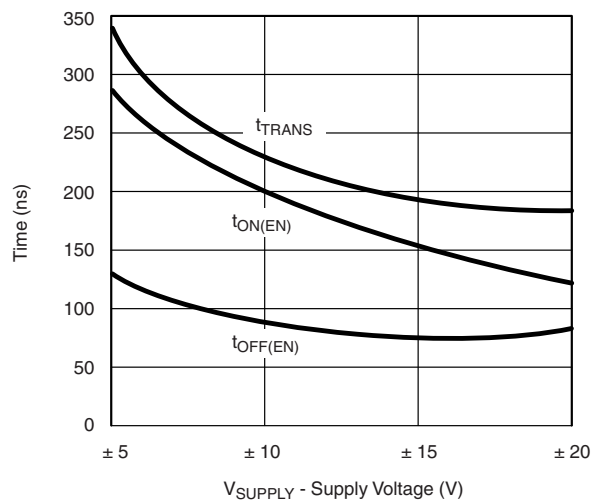
$R_{DS(on)}$ vs. V_D and Supply



I_D , I_S Leakage Currents vs. Analog Voltage



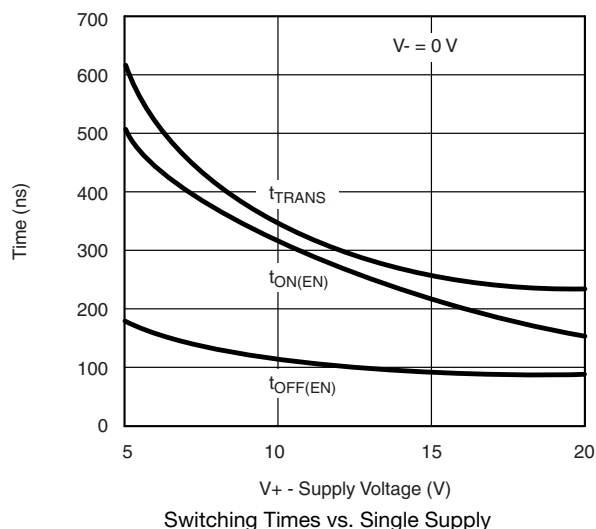
I_D , I_S Leakages vs. Temperature



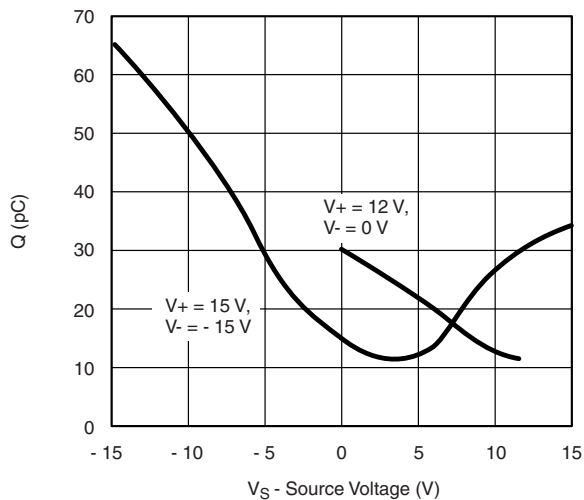
Switching Times vs. Bipolar Supplies



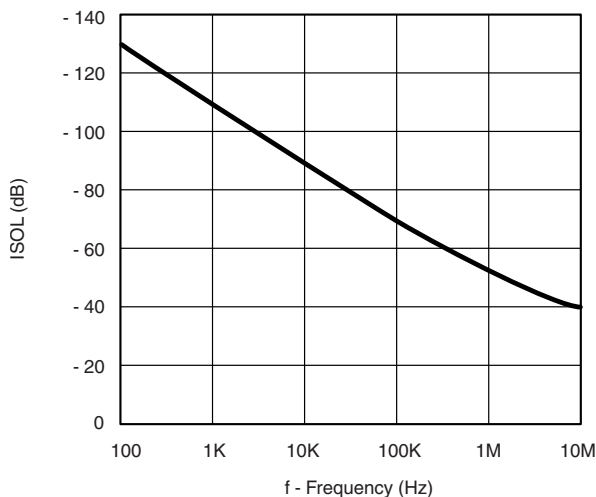
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)



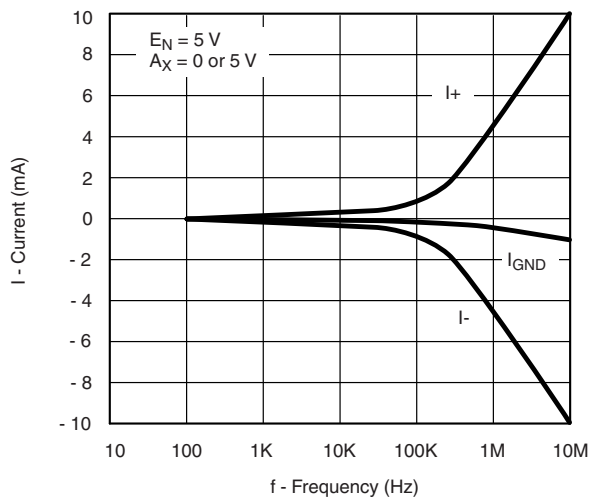
Switching Times vs. Single Supply



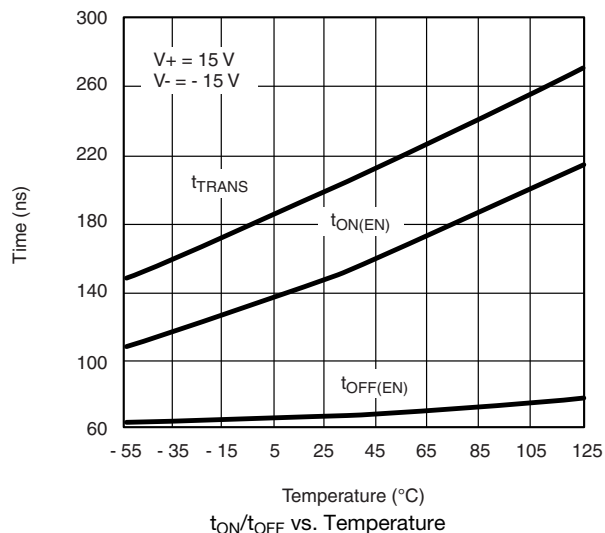
Charge Injection vs. Analog Voltage



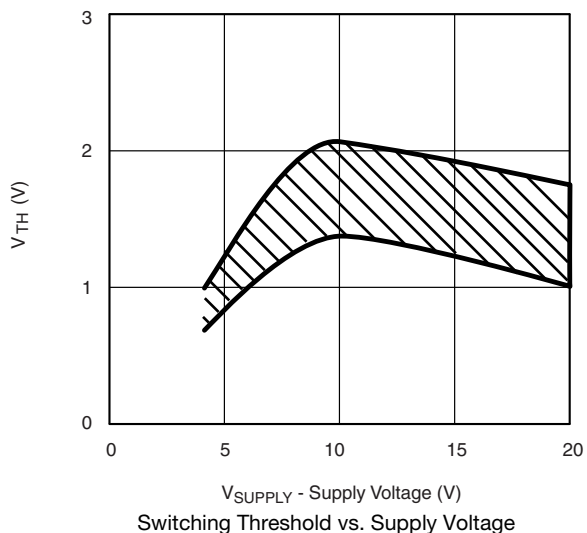
Off-Isolation vs. Frequency



Supply Currents vs. Switching Frequency



$t_{\text{ON}}/t_{\text{OFF}}$ vs. Temperature



Switching Threshold vs. Supply Voltage

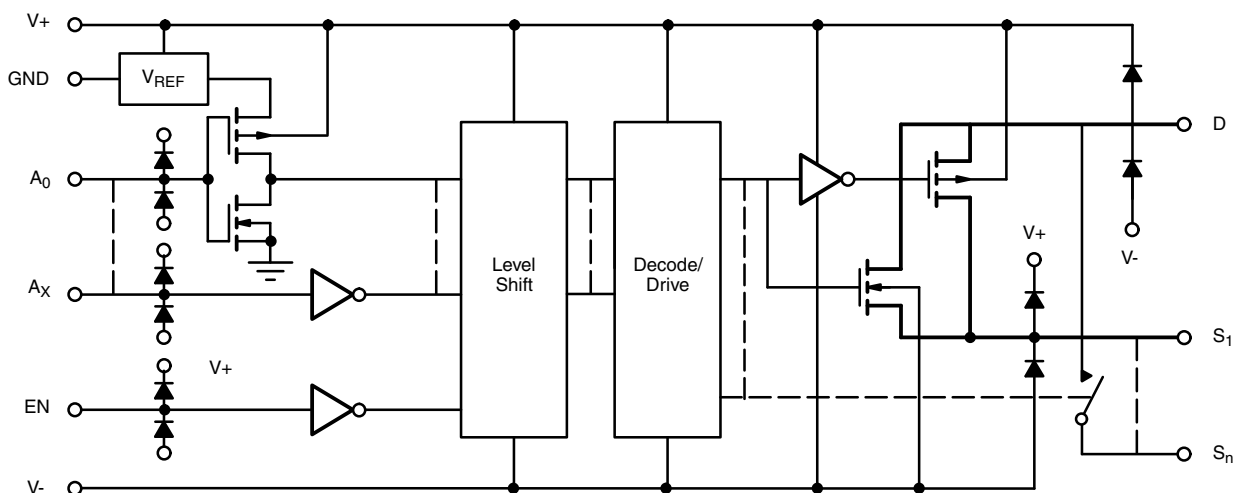
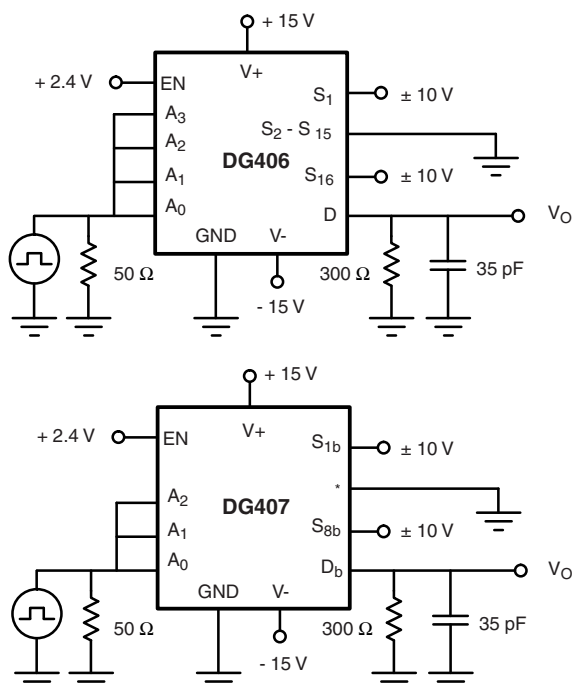
SCHEMATIC DIAGRAM (Typical Channel)


Fig. 1

TEST CIRCUITS


* = S_{1a} - S_{8a}, S_{2b} S_{±7b}, D_a

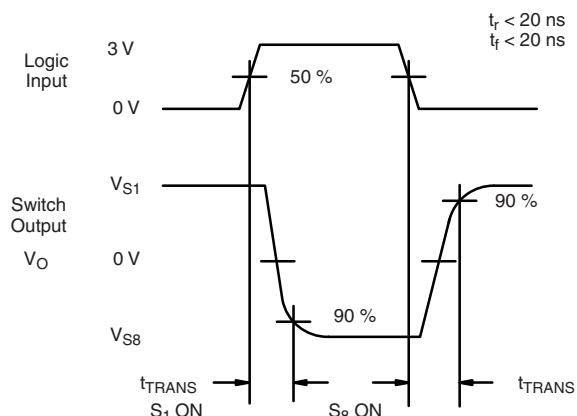


Fig. 2 - Transition Time

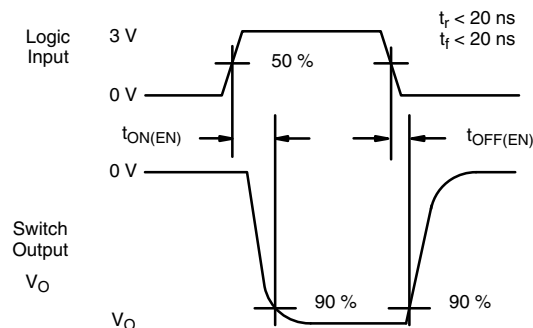
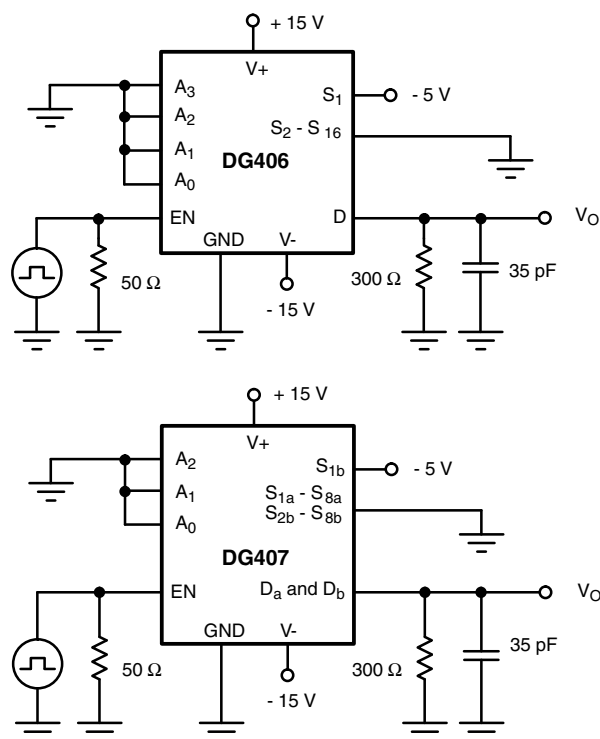
TEST CIRCUITS


Fig. 3 - Enable Switching Time

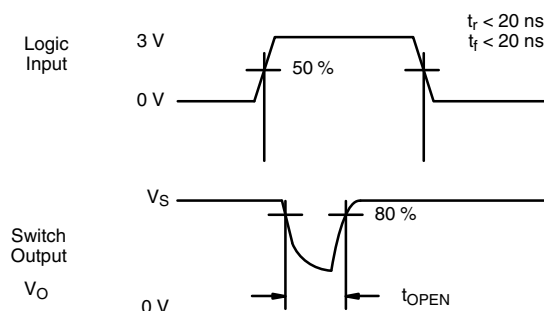
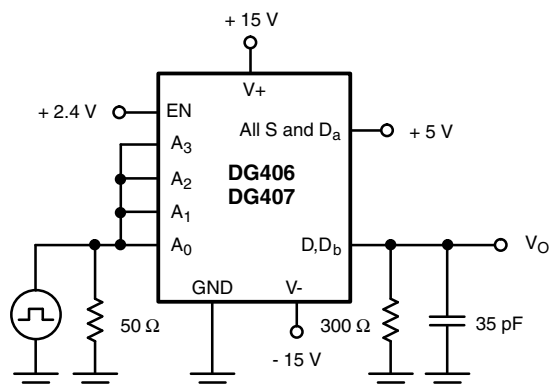


Fig. 4 - Break-Before-Make Interval

APPLICATIONS HINTS

Sampling speed is limited by two consecutive events: the transition time of the multiplexer, and the settling time of the sampled signal at the output.

t_{TRANS} is given on the data sheet. Settling time at the load depends on several parameters: $R_{\text{DS(on)}}$ of the multiplexer, source impedance, multiplexer and load capacitances, charge injection of the multiplexer and accuracy desired.

The settling time for the multiplexer alone can be derived from the model shown in figure 5. Assuming a low impedance signal source like that presented by an op amp or a buffer amplifier, the settling time of the RC network for a given accuracy is equal to $n\tau$:

% ACCURACY	# BITS	N
0.25	8	6
0.012	12	9
0.0017	15	11

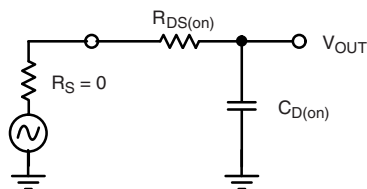


Fig. 5 - Simplified Model of One Multiplexer Channel

The maximum sampling frequency of the multiplexer is:

$$f_s = \frac{1}{N(t_{\text{SETTLING}} + t_{\text{TRANS}})} \quad (1)$$

where N = number of channels to scan

$$t_{\text{SETTLING}} = n\tau = n \times R_{\text{DS(on)}} \times C_{\text{D(on)}}$$

For the DG406 then, at room temp and for 12-bit accuracy, using the maximum limits:

$$f_s = \frac{1}{16(9 \times 100 \Omega \times 10^{-12} \text{F}) + 300 \times 10^{-12} \text{s}} \quad (2)$$

or

$$f_s = 694 \text{ kHz} \quad (3)$$

From the sampling theorem, to properly recover the original signal, the sampling frequency should be more than twice the maximum component frequency of the original signal. This assumes perfect bandlimiting. In a real application sampling at three to four times the filter cutoff frequency is a good practice.

Therefore from equation 2 above:

$$f_c = \frac{1}{4} \times f_s = 173 \text{ kHz} \quad (4)$$

From this we can see that the DG406 can be used to sample 16 different signals whose maximum component frequency can be as high as 173 kHz. If for example, two channels are used to double sample the same incoming signal then its cutoff frequency can be doubled.

The block diagram shown in figure 6 illustrates a typical data acquisition front end suitable for low-level analog signals. Differential multiplexing of small signals is preferred since this method helps to reject any common mode noise. This is especially important when the sensors are located at a distance and it may eliminate the need for individual amplifiers. A low $R_{\text{DS(on)}}$, low leakage multiplexer like the DG407 helps to reduce measurement errors. The low power dissipation of the DG407 minimizes on-chip thermal gradients which can cause errors due to temperature mismatch along the parasitic thermocouple paths. Please refer to Application Note AN203 for additional information.

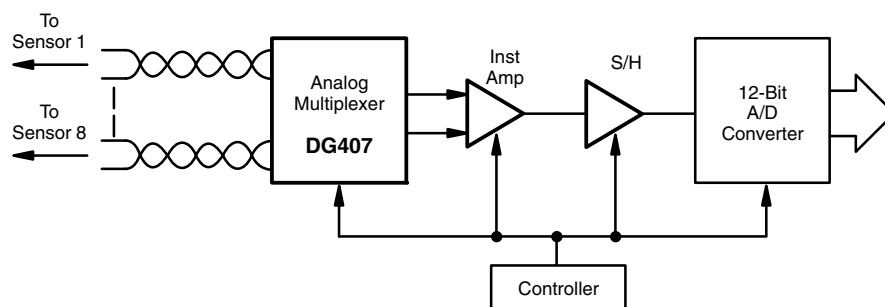
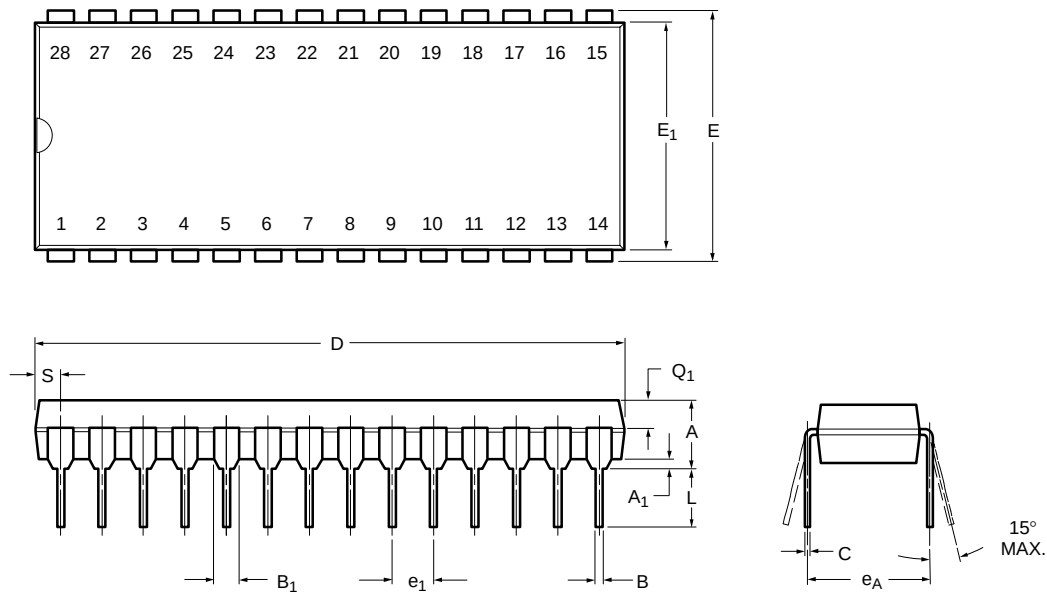


Fig. 6 - Measuring Low-Level Analog Signals is more accurate when using a Differential Multiplexing Technique

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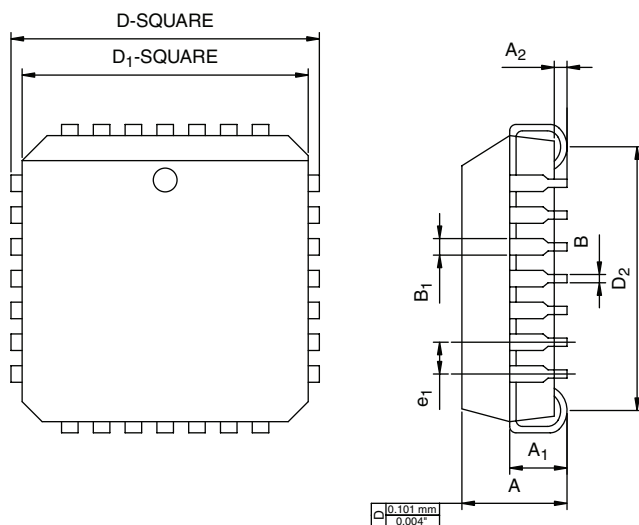
PDIP: 28-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	2.29	5.08	0.090	0.200
A₁	0.39	1.77	0.015	0.070
B	0.38	0.56	0.015	0.022
B₁	0.89	1.65	0.035	0.065
C	0.204	0.30	0.008	0.012
D	35.10	39.70	1.380	1.565
E	15.24	15.88	0.600	0.625
E₁	13.21	14.73	0.520	0.580
e₁	2.29	2.79	0.090	0.110
e_A	14.99	15.49	0.590	0.610
L	2.60	5.08	0.100	0.200
Q₁	0.95	2.345	0.0375	0.0925
S	0.995	2.665	0.0375	0.105

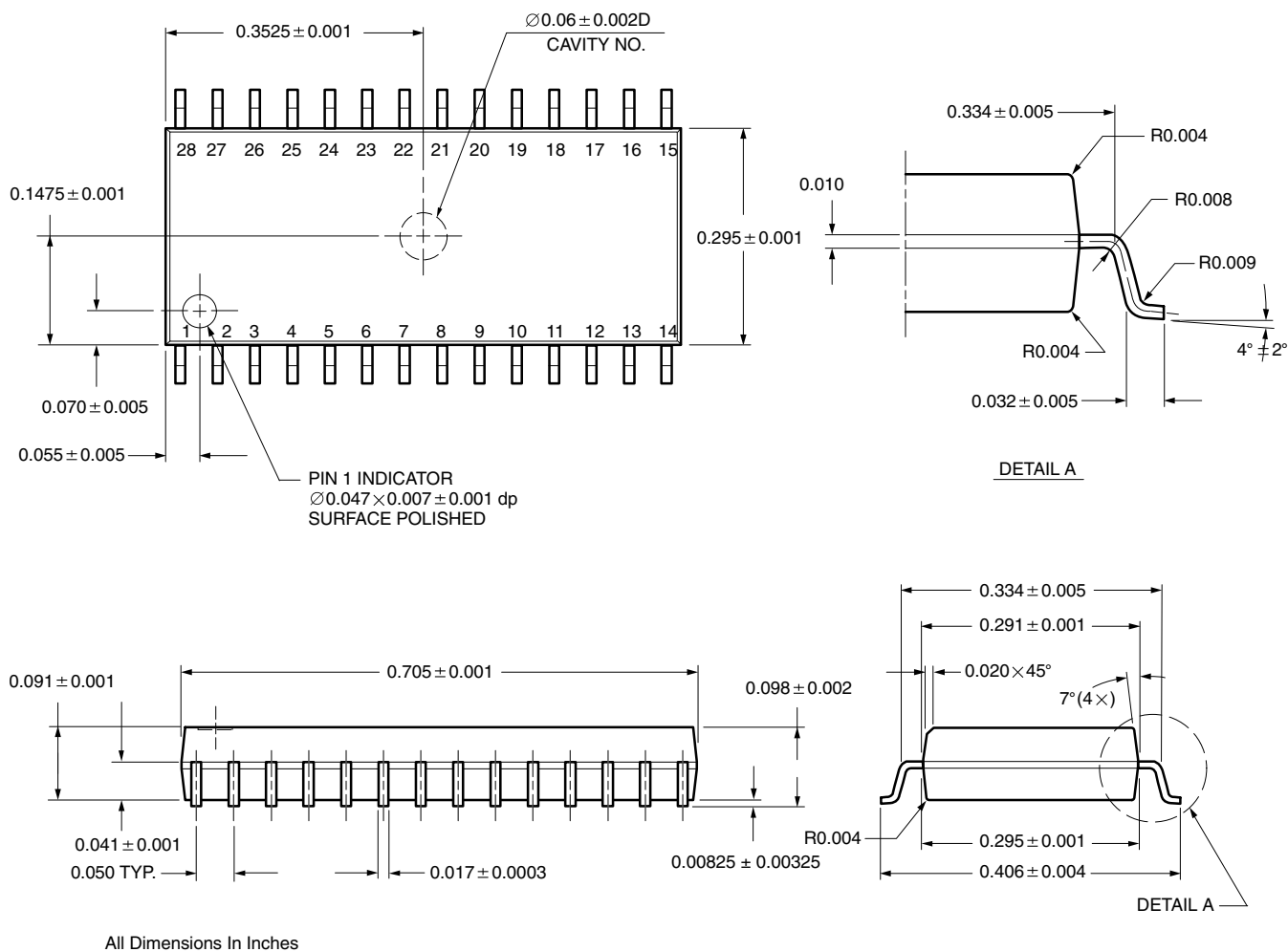
ECN: S-03946—Rev. F, 09-Jul-01
DWG: 5488

PLCC: 28-LEAD



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.20	4.57	0.165	0.180
A ₁	2.29	3.04	0.090	0.120
A ₂	0.51	-	0.020	-
B	0.331	0.553	0.013	0.021
B ₁	0.661	0.812	0.026	0.032
D	12.32	12.57	0.485	0.495
D ₁	11.430	11.582	0.450	0.456
D ₂	9.91	10.92	0.390	0.430
e ₁	1.27 BSC		0.050 BSC	
ECN: T09-0766-Rev. D, 28-Sep-09 DWG: 5491				

SOIC (WIDE-BODY): 28-LEADS



ECN: E11-2209-Rev. D, 01-Aug-11
DWG: 5850



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